

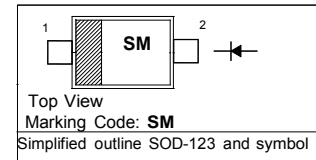
Surface Mount Schottky Barrier Diodes

Features

- Low forward voltage
- Low reverse capacitance

PINNING

PIN	DESCRIPTION
1	Cathode
2	Anode



Absolute Maximum Ratings ($T_a = 25\text{ }^\circ\text{C}$)

Parameter	Symbol	Value	Unit	
Peak Repetitive Reverse Voltage	SD101AW	60	V	
	SD101BW	50		
	SD101CW	40		
Reverse Voltage	SD101AW	60	V	
	SD101BW	50		
	SD101CW	40		
Forward Continuous Current	I_{FM}	15	mA	
Power Dissipation	P_d	400	mW	
Non-Repetitive Peak Forward Surge Current	I_{FSM}	at $t = 1\text{ s}$	50	mA
		at $t = 10\text{ }\mu\text{s}$	2	A
Operating and Storage Temperature Range	T_j, T_{stg}	- 65 to + 125	$^\circ\text{C}$	

Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
Reverse Breakdown Voltage at $I_R = 10\text{ }\mu\text{A}$	SD101AW	60	-	V
	SD101BW	50	-	
	SD101CW	40	-	
Forward Voltage at $I_F = 1\text{ mA}$ at $I_F = 15\text{ mA}$	SD101AW	-	0.41	V
	SD101BW	-	0.4	
	SD101CW	-	0.39	
	SD101AW	-	1	
	SD101BW	-	0.95	
	SD101CW	-	0.9	
Reverse Current at $V_R = 50\text{ V}$ at $V_R = 40\text{ V}$ at $V_R = 30\text{ V}$	SD101AW	-	200	nA
	SD101BW	-	200	
	SD101CW	-	200	
Total Capacitance at $V_R = 0\text{ V}$, $f = 1\text{ MHz}$	SD101AW	-	2	pF
	SD101BW	-	2.1	
	SD101CW	-	2.2	
Reverse Recovery Time at $I_F = I_R = 5\text{ mA}$, $I_{rr} = 0.1X I_R$, $R_L = 100\text{ }\Omega$	t_{rr}	-	1	ns



CHINA BASE
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SOD-123



SD101AW-SD101CW

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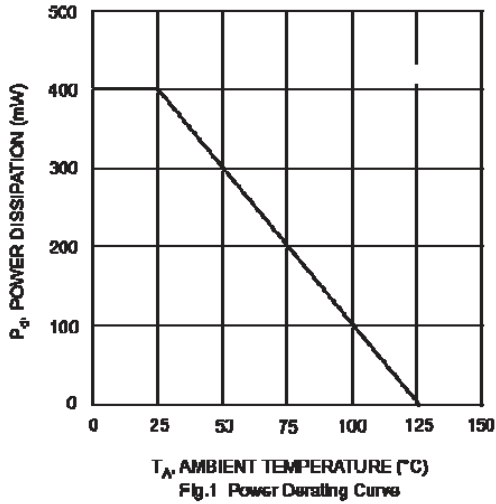


Fig. 1 Power Derating Curve

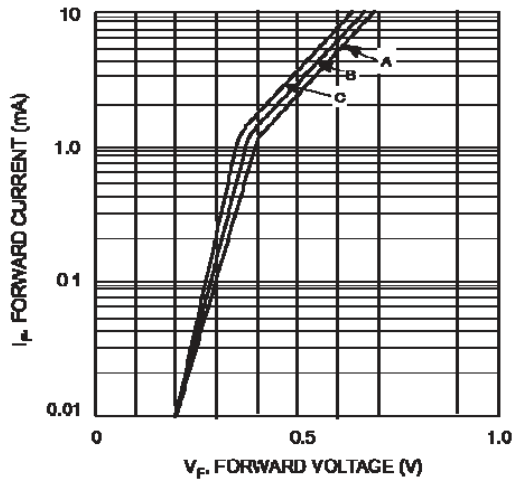


Fig. 2 Typical Forward Characteristic

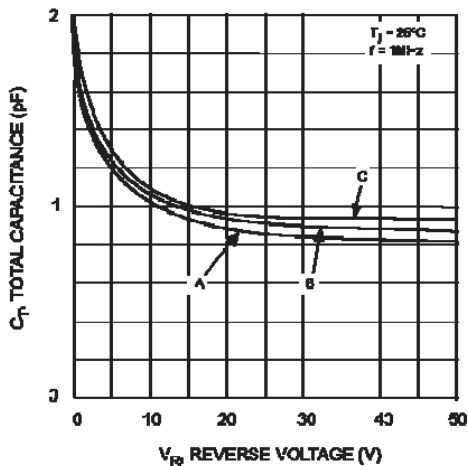


Fig. 3 Typical Total Capacitance vs Reverse Voltage

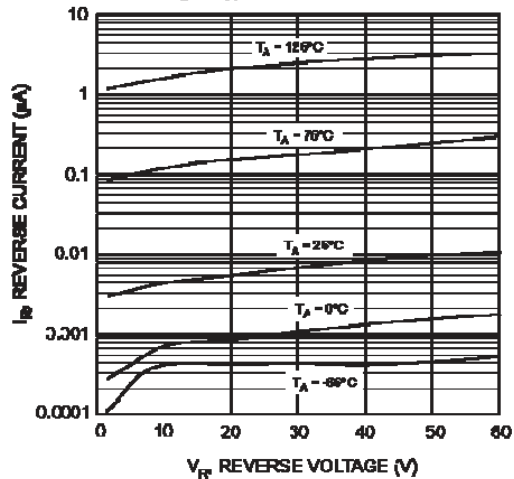


Fig. 4 Typical Reverse Characteristics